AMENDMENTS TO THE CLAIMS:

Following is a listing of all claims in the present application, which listing supersedes all previously presented claims:

1-5. (Cancelled)

6. (Currently Amended) An apparatus for cleaning a semiconductor wafer, comprising:

a chamber in which a wafer is mounted;

a revolving ~~chuck,~~chuck mounted in the chamber for supporting and fixing the wafer;

a nozzle for spraying cleaning solution onto the wafer;

a cover for covering an upper part of the chamber;

a ~~light source,~~laser fixed on an upper part of the cover for heating the wafer and the cleaning solution;~~solution during cleaning of the wafer;~~

a focusing lens for condensing a beam emitted from the ~~light source~~laser onto the wafer; and

a cooling water conduit surrounding an external wall of the cover for cooling the cover, the wafer, and the cleaning solution.~~an antipollution plate mounted between a lower part of the focusing lens and a upper part of the nozzle for preventing the focusing lens from being polluted by the cleaning solution.~~

7. (Cancelled)

8. (Currently Amended) The apparatus according to ~~claim 6,~~claim 25, wherein the antipollution plate is made of transparent quartz or sapphire.

9. (Currently Amended) The apparatus according to ~~claim 21,~~claim 6, wherein the laser is an ultraviolet, an infrared, or a visible ray laser.

10. (Original) The apparatus according to claim 6, wherein the cleaning solution is ozone water, hydrogen water, or electrolytic-ionized water.

11. (Cancelled)

12. (Currently Amended) A method for cleaning a ~~wafer,~~wafer using an apparatus for cleaning a semiconductor wafer according to claim 6, the method comprising:

rotating the wafer at a predetermined speed;

spraying cleaning solution onto the wafer through a nozzle;

heating the wafer and the cleaning solution by the laser; and

cleaning the wafer.~~a light source;~~

~~using a lens to focus light from the light source onto the wafer or the cleaning solution; and~~

~~providing an antipollution plate between the nozzle and the focusing lens to prevent the cleaning solution from reaching the focusing lens.~~

13. (Cancelled)

14. (Original) The method according to claim 12, wherein the cleaning solution is ozone water, hydrogen water, or electrolytic-ionized water.

15. – 21. (Cancelled)

22. (Previously Presented) The method according to claim 12, further comprising controlling a rotational speed of the wafer.

23. (Currently Amended) The method according to claim 12, further comprising controlling a power of the laser.~~light source.~~

24. (Previously Presented) The method according to claim 12, further comprising controlling an amount of cleaning solution.

25. (New) The apparatus according to claim 6, further comprising an antipollution plate mounted on a lower part of the focusing lens inside the cover for preventing the focusing lens from being polluted by the cleaning solution.